

Yonghan Roh

List of Publications by Year in descending order

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65
papers

734
citations

567281

15
h-index

580821

25
g-index

66
all docs

66
docs citations

66
times ranked

1033
citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of floating gate dry etching on erase characteristics in NOR flash memory. IEEE Electron Device Letters, 2002, 23, 476-478.	3.9	89
2	n- and p-Type Doping Phenomenon by Artificial DNA and M-DNA on Two-Dimensional Transition Metal Dichalcogenides. ACS Nano, 2014, 8, 11603-11613.	14.6	85
3	Argon and nitrogen implantation effects on the structural and optical properties of vacuum evaporated cadmium sulphide thin films. Semiconductor Science and Technology, 2002, 17, 97-103.	2.0	54
4	Effects of deposition parameters on the crystallinity of CeO ₂ thin films deposited on Si(100) substrates by r.f.-magnetron sputtering. Thin Solid Films, 2000, 360, 154-158.	1.8	52
5	Coverage Control of DNA Crystals Grown by Silica Assistance. Angewandte Chemie - International Edition, 2011, 50, 9145-9149.	13.8	36
6	Formation of λ-DNA's in Parallel- and Crossed-Line Arrays by Molecular Combing and Scanning-Probe Lithography. Nano Letters, 2006, 6, 1334-1338.	9.1	27
7	Formation of Reliable HfO ₂ /HfSi _x O _y Gate-Dielectric for Metal-Oxide-Semiconductor Devices. Japanese Journal of Applied Physics, 2002, 41, 6904-6907.	1.5	25
8	The Hysteresis Caused by Interface Trap and Anomalous Positive Charge in Al/CeO ₂ -SiO ₂ /Silicon Capacitors. Japanese Journal of Applied Physics, 1997, 36, L1681-L1684.	1.5	22
9	Size-Controllable DNA Rings with Copper-Ion Modification. Small, 2012, 8, 374-377.	10.0	22
10	Poly-4-vinylphenol and poly(melamine-co-formaldehyde)-based graphene passivation method for flexible, wearable and transparent electronics. Nanoscale, 2014, 6, 3830.	5.6	21
11	The effect of deposition temperature on the electrical and physical properties of the Ba(Zr,Ti)O ₃ thin films. Journal of Non-Crystalline Solids, 2002, 303, 190-193.	3.1	20
12	Selective Formation of a Latticed Nanostructure with the Precise Alignment of DNA-Templated Gold Nanowires. Langmuir, 2010, 26, 18315-18319.	3.5	18
13	Controlled gold nanoparticle assembly on DNA molecule as template for nanowire formation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1327-1331.	2.1	17
14	Significant reduction of leakage current in the TiO ₂ /Si structure by the insertion of the CeO ₂ intermediate layer. Applied Physics Letters, 2000, 77, 729-731.	3.3	15
15	Partial Crystallization of HfO ₂ for Two-Bit/Four-Level SONOS-Type Flash Memory. IEEE Transactions on Electron Devices, 2007, 54, 3177-3185.	3.0	15
16	Fabrication and characterization of DNA-templated conductive gold nanoparticle chains. Journal of Applied Physics, 2009, 105, 074302.	2.5	15
17	Formation of nanometer-scale structures using conventional optical lithography. Thin Solid Films, 2008, 516, 1489-1492.	1.8	14
18	Electrical Characterizations of HfO ₂ /Al ₂ O ₃ /Si as Alternative Gate Dielectrics. Journal of the Korean Physical Society, 2007, 51, 238.	0.7	13

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19	Formation of nanometer-scale gap electrodes based on a plasma ashing technique. <i>Thin Solid Films</i> , 2006, 515, 744-747.	1.8	11
20	Fabrication of SiO ₂ nano-dots by block copolymer lithography and liquid phase deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 147, 209-212.	3.5	11
21	Selective Alignment of Gold Nanowires Synthesized With DNA as Template by Surface-Patterning Technique. <i>IEEE Nanotechnology Magazine</i> , 2010, 9, 254-257.	2.0	11
22	Fabrication of Highly Uniform Conductive Polypyrrole Nanowires with DNA Template. <i>Journal of Nanoscience and Nanotechnology</i> , 2010, 10, 3180-3184.	0.9	9
23	Analysis of Hysteresis Observed in Multi-Layered MoS ₂ Field Effect Transistors. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 7327-7330.	0.9	9
24	Analysis of asymmetrical hysteresis phenomena observed in TMD-based field effect transistors. <i>AIP Advances</i> , 2018, 8, .	1.3	8
25	Roles of buffer solution and substrate surface on the characteristic of DNA network formed on SiO ₂ . <i>Materials Science and Engineering C</i> , 2003, 23, 851-855.	7.3	7
26	Effect of calcination on the crystallinity of sputtered TiO ₂ thin films as studied by Raman scattering. <i>Crystal Research and Technology</i> , 2005, 40, 222-225.	1.3	7
27	Roles of Residual Stress in Dynamic Refresh Failure of a Buried-Recessed-Channel-Array Transistor (B-CAT) in DRAM. <i>IEEE Electron Device Letters</i> , 2016, 37, 859-861.	3.9	7
28	Properties of HfO ₂ /Hf-Silicate/Si Structures with Hf-Silicate Formed by Hf Metal Deposition and Subsequent Reaction. <i>Japanese Journal of Applied Physics</i> , 2001, 40, L813-L816.	1.5	6
29	Effect of post-fabrication thermal annealing on Fermi-level pinning phenomenon in metal-pentacene junctions. <i>Organic Electronics</i> , 2012, 13, 1511-1515.	2.6	6
30	Leakage current reduction in pentacene-based thin film transistor using asymmetric source/drain electrodes. <i>Organic Electronics</i> , 2012, 13, 1056-1059.	2.6	6
31	Post-etch residue removal in BCB/Cu interconnection structure. <i>Thin Solid Films</i> , 2003, 435, 238-241.	1.8	5
32	Selective Growth of the Silicon-Oxide Nanodot Array Using Nanosphere Lithography and Liquid-Phase Deposition. <i>IEEE Nanotechnology Magazine</i> , 2010, 9, 361-366.	2.0	5
33	Structural and functional stabilities of artificially designed DNA ultra-thin films grown by silica Assistance. <i>Current Applied Physics</i> , 2012, 12, 1207-1211.	2.4	5
34	Silicon Dioxide Deposited by Using Liquid Phase Deposition at Room Temperature for Nanometer-Scaled Isolation Technology. <i>Journal of the Korean Physical Society</i> , 2007, 51, 1191.	0.7	5
35	Electrical Characteristics of Al/CeO ₂ (200)/Si(100) and Al/CeO ₂ (111)/Si(100) Metal-Insulator-Semiconductor Structure. <i>Japanese Journal of Applied Physics</i> , 2001, 40, L564-L566.	1.5	4
36	Electrical characteristics of oxygen doped DNA molecules. <i>Thin Solid Films</i> , 2011, 519, 7057-7059.	1.8	4

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37	Characteristics of fabricated catalytic combustible micro gas sensor with low power consumption for detecting methane leakage of compressed natural gas bus. <i>Journal of Electroceramics</i> , 2013, 31, 280-285.	2.0	4
38	Depth-controllable ultra shallow Indium Gallium Zinc Oxide/Gallium Arsenide hetero junction diode. <i>Journal of Alloys and Compounds</i> , 2013, 561, 228-230.	5.5	4
39	Improvement of Quantum Dot Light Emitting Device Characteristics by CdSe/ZnS Blended with HMDS (Hexamethyldisilazane). <i>Applied Sciences (Switzerland)</i> , 2020, 10, 6081.	2.5	4
40	Characteristics of Hf-silicate Interfacial Layers Formed by WetEtching. <i>Journal of the Korean Physical Society</i> , 2009, 55, 1022-1025.	0.7	4
41	Hysteresis caused by defects in buffer layer of metal-ferroelectric-insulator-semiconductor (MFIS) devices. <i>Integrated Ferroelectrics</i> , 2001, 40, 245-254.	0.7	3
42	Performance and characteristics of imprint mould fabricated by liquid-phase deposition. <i>Superlattices and Microstructures</i> , 2008, 44, 520-527.	3.1	3
43	FN-degradation of S-RCAT with different grain size and oxidation method. <i>Microelectronic Engineering</i> , 2014, 119, 32-36.	2.4	3
44	The improvement of the SiO ₂ /InAs interface properties with the aid of fast electron irradiation in a direct current sputter deposition system. <i>Applied Surface Science</i> , 2001, 172, 295-300.	6.1	2
45	Influence of plasma edge damage on erase characteristics of NOR flash EEPROM using channel erase method. , 0, , .		2
46	Characteristics of gold nanowires and UV spectral changes by interaction between gold nanoparticles and DNA. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 2545-2550.	2.7	2
47	Characteristics of Ultrashallow Hetero Indium-Gallium-Zinc-Oxide/Germanium Junction. <i>IEEE Electron Device Letters</i> , 2012, 33, 1363-1365.	3.9	2
48	Negative effect of Au nanoparticles on an IGZO TFT-based nonvolatile memory device. <i>Journal of the Korean Physical Society</i> , 2014, 64, 337-340.	0.7	2
49	Electrical characterizations of MgTiO ₃ thin films grown on Si. <i>Integrated Ferroelectrics</i> , 2000, 31, 359-366.	0.7	1
50	Selective liquid phase deposition of silicon oxide at low temperature for nanometer-scale structures. <i>Thin Solid Films</i> , 2009, 517, 3947-3949.	1.8	1
51	Electrical Characteristics and Doping Mechanism of DNA Molecules Doped with Iodine Solutions. <i>Journal of Nanoscience and Nanotechnology</i> , 2010, 10, 3484-3488.	0.9	1
52	Uniform formation of Au coated polystyrene core-shell structure using metallization process. <i>Thin Solid Films</i> , 2011, 519, 7120-7123.	1.8	1
53	Assembling CdSe/ZnS core-shell quantum dots on localized DNA nanostructures. <i>RSC Advances</i> , 2014, 4, 53201-53205.	3.6	1
54	Off-state degradation with ac bias in PMOSFET. <i>Microelectronics Reliability</i> , 2016, 65, 16-19.	1.7	1

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55	Improving Charge-Imbalanced Problem of Quantum Dot Light-Emitting Diodes with TPBi/ZnO Electron Transport Layer. Journal of Nanoscience and Nanotechnology, 2019, 19, 6152-6157.	0.9	1
56	Improving hole injection ability using a newly proposed WO ₃ /NiO _x bilayer in solution processed quantum dot light-emitting diodes. Current Applied Physics, 2022, 38, 81-90.	2.4	1
57	Analysis of Current Components Observed by Cyclic Current-Voltage Measurement in Metal-Oxide-Semiconductor Capacitors. Japanese Journal of Applied Physics, 2000, 39, L1152-L1154.	1.5	0
58	Electrical characteristics of CeO ₂ /sub 2/ buffer layer for a FRAM. , 0, , .		0
59	Electrical properties of the MOS structures using strained (Ba _{0.5} , Sr _{0.5})TiO ₃ thin films. Ferroelectrics, 2001, 259, 269-275.	0.6	0
60	Asymmetrical Increase of Memory Window in MFIS Devices After Avalanche Hole Injection. Ferroelectrics, 2005, 329, 113-118.	0.6	0
61	Improved performance of multi-giga bit NAND flash using channel orientation. , 2006, , .		0
62	Analysis of dynamic retention characteristics of NWL scheme in high density DRAM. , 2013, , .		0
63	Effect of body bias on negative bias temperature instability in pMOSFET with SiON gate dielectrics. Solid-State Electronics, 2014, 91, 127-129.	1.4	0
64	Formation of Au Nanowires using DNA Molecules as Template. Journal of the Korean Physical Society, 2009, 55, 1892-1895.	0.7	0
65	Triple boron doped silicon for selective epitaxial growth of 3D NAND flash memory. Journal of the Korean Physical Society, 0, , 1.	0.7	0